



## DP0640LB&amp;DP0640SB

半导体放电管

版本号  
201603-A

## 产品概述

半导体放电管是一种过压保护器件，是利用晶闸管原理制成的，依靠PN结的击穿电流触发器件导通放电，可以流过很大的浪涌电流或脉冲电流。

## 产品特点

- 双向过电压电路保护
- 抗浪涌能力强
- 快速反应，可恢复
- 漏电小，可靠性高
- 低电容

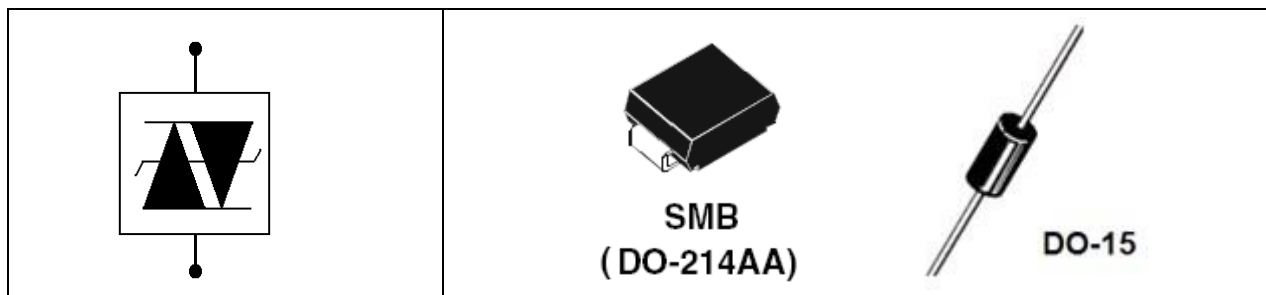
## 特征参数

## 应用领域

符号	额定值	单位
$V_{DRM}$	58	V
$V_S$	77	V
$I_H$	150	mA

DP0640半导体放电管主要应用于通讯设备的过电压防护；家用电器，工控仪器的过电压防护。

封装：SMB (DO-214AA)，DO-15



## 电参数

参数名称	符号	测试条件	规范值			单位
			最小	典型	最大	
不动作电压	$V_{DRM}$	$I=5\mu A$	58			V
不动作电流	$I_{DRM}$	$V=V_{DRM}$ 额定值			5	$\mu A$
跃变电压	$V_S$	100KV/s			77	V
跃变电流	$I_S$	100KV/s			800	mA
维持电流	$I_H$	10A, 10/1000 $\mu s$	150			mA
通态电压	$V_T$	$I_T=2.2A$			4	V
通态电流	$I_T$	额定值		2.2		A
极间电容	$C_o$	1MHz, 2V偏置			80	pF
峰值浪涌电流	$I_{PP}$	10/1000 $\mu s$			80	A

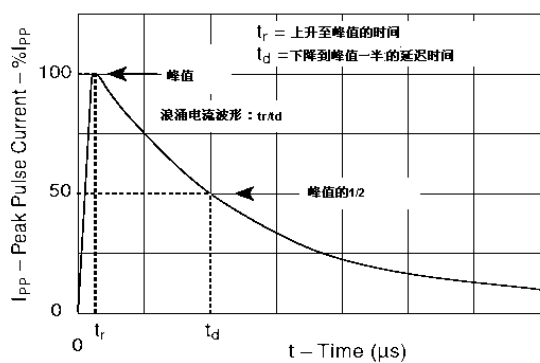
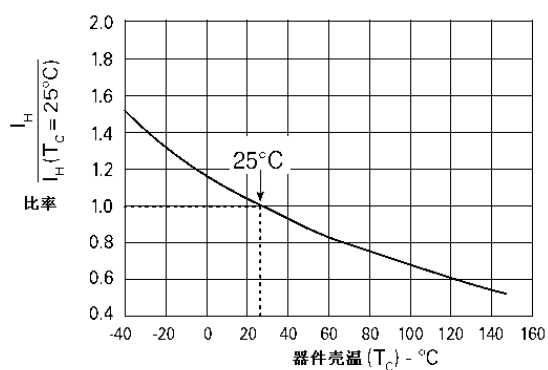
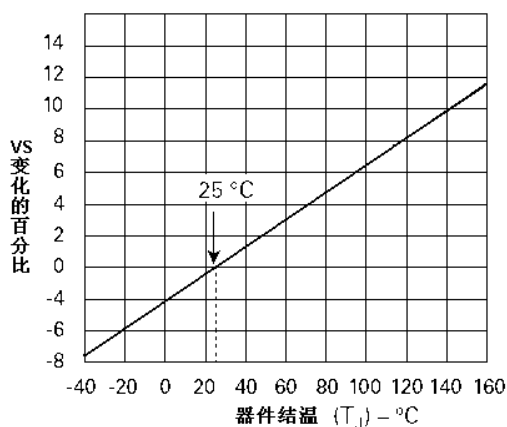
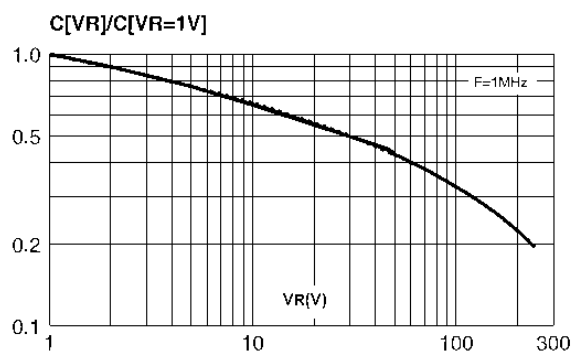


## ■ 热特性

符号	参数	数值	单位
$T_J$	工作结温范围	-40~+150	°C
$T_S$	贮存温度范围	-65~+150	°C

## ■ 典型特性曲线

浪涌电流波形

 $I_H$  随温度变化率 $V_S$  随结温变化率 $C_o$  随偏置电压的变化率 (相对于  $V_R=1V$ )



### 封装尺寸

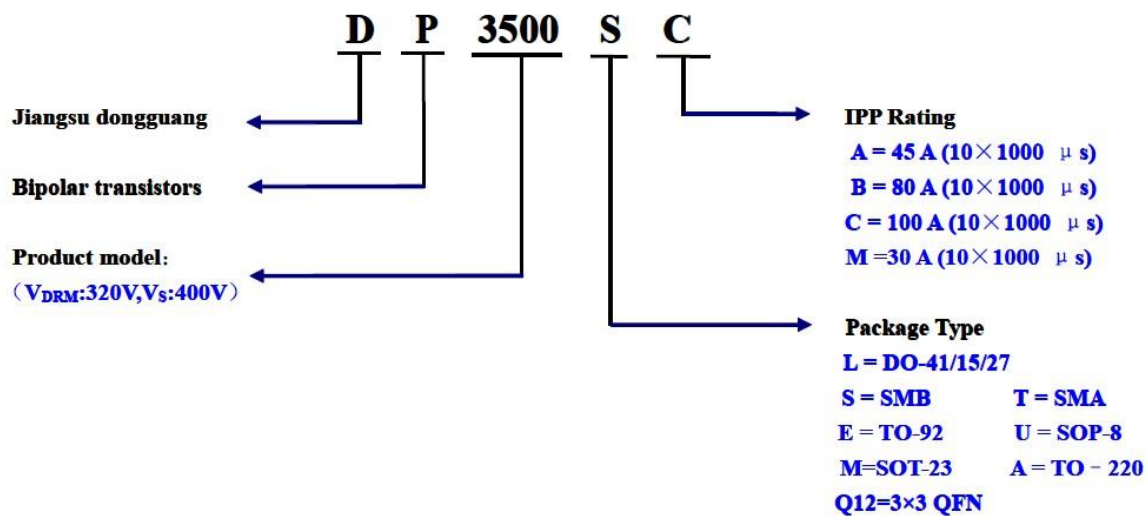
**SMB**  
**(DO-214AA)**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.40	0.006	0.016
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.50	0.030	0.059

**DO-15**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	6.05	6.75	0.238	0.266
B	2.95	3.53	0.116	0.139
C	26	31	1.024	1.220
D	0.71	0.88	0.028	0.035

### 命名规则





## DP0640LB&amp;DP0640SB



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## Description

The SDT is a kind of overvoltage protection device. It is designed at the PNP structure. High pulse current can cross SDT.

## Features and Benefits

- Low voltage and overshoot
- Low on-state voltage
- Does not degrade with use
- Fails short circuit when surged in excess of ratings
- Low capacitance

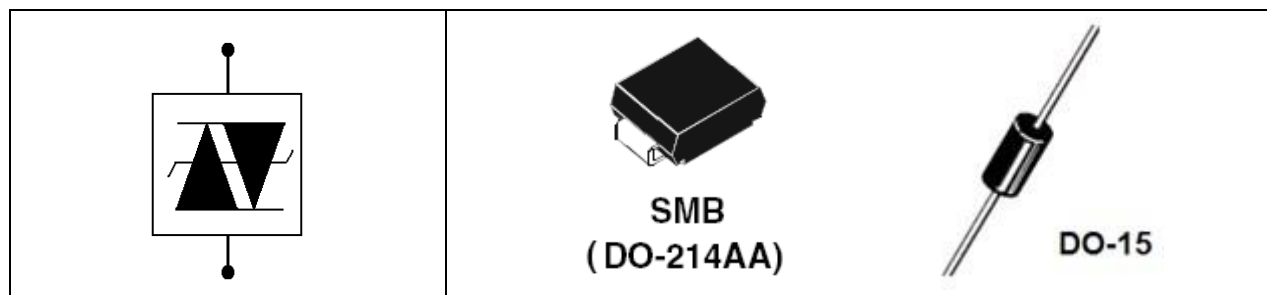
## Characteristic parameters

## 应用领域

symbol	Rated value	unit
$V_{DRM}$	58	V
$V_S$	77	V
$I_H$	150	mA

DP0640 are designed to protect communication equipment, appliances and Industrial And Control Instrumentation Equipment from damaging overvoltage transients.

Package : SMB (DO-214AA), DO-15



## Electrical Parameters

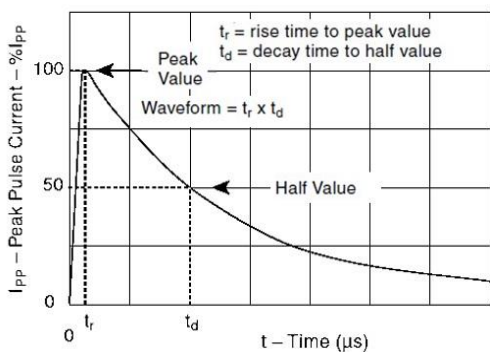
Parameter	symbol	Test conditions	Value			unit
			Min.	Typ.	Max.	
Leakage Voltage	$V_{DRM}$	$I=5\mu A$	58			V
Leakage Current	$I_{DRM}$	$V=V_{DRM}$			5	$\mu A$
Switching Voltage	$V_S$	100KV/s			77	V
Switching Current	$I_S$	100KV/s			800	mA
Holding Current	$I_H$	10A, 10/1000 $\mu s$	150			mA
On-state Voltage	$V_T$	$I_T=2.2A$			4	V
On-state Current	$I_T$	Rating value		2.2		A
Off-state Capacitance	$C_o$	1MHz, 2V offset			80	pF
Peak Pulse Current	$I_{PP}$	10/1000 $\mu s$			80	A

■ 热特性

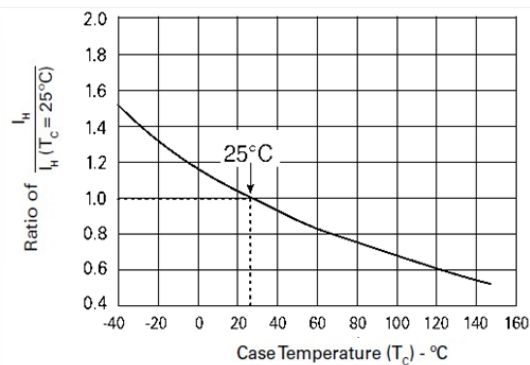
Symbol	Parameter	Value	Unit
$T_J$	Operating Junction Temperature	-40~+150	°C
$T_S$	Storage Temperature Range	-65~+150	°C

■ Typical characteristic curve

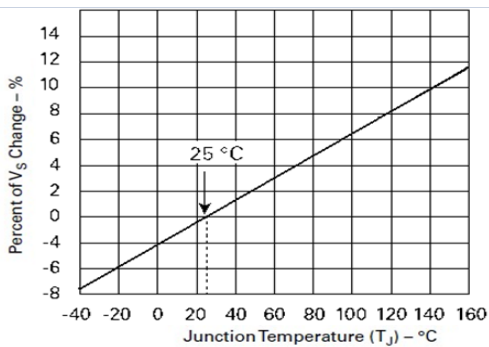
Tr x Td Pulse waveform



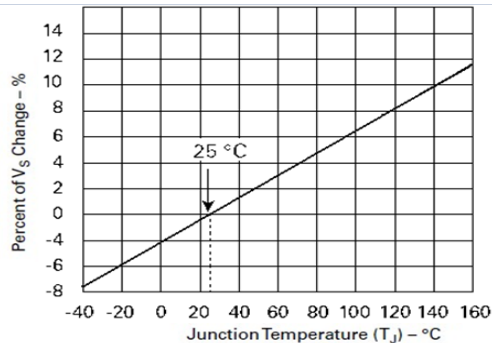
Normalized DC holding current vs. case temperature



Vs change vs. junction temperature



Co change vs. bias voltage ( $V_R=1V$ )





### Package size

**SMB**  
**(DO-214AA)**

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**DO-15**

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B	2.95	3.53	0.116	0.139
C	26	31	1.024	1.220
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### Naming Rule

